

N-channel TrenchMOS standard level FET Rev. 04 — 8 June 2010

**Product data sheet** 

#### **Product profile** 1.

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

- 1.3 Applications
  - 12 V loads
  - Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	75	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2		-	-	300	W
Static cha	aracteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \overline{Figure \ 11}; \\ \text{see } \overline{Figure \ 12} \end{array}$		-	2.3	2.7	mΩ
Avalanch	e ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A};  \text{V}_{\text{sup}} \leq 30 \text{ V}; \\ R_{\text{GS}} &= 50  \Omega;  \text{V}_{\text{GS}} = 10  \text{V}; \\ T_{\text{j(init)}} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $		-	-	2.3	J
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 24 \text{ V}; T_j = 25 \text{ °C};$ see Figure 13		-	29	-	nC

[1] Continuous current is limited by package.

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### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	_	<u>_</u>
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK762R7-30B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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### 4. Limiting values

#### Table 4. Limiting values

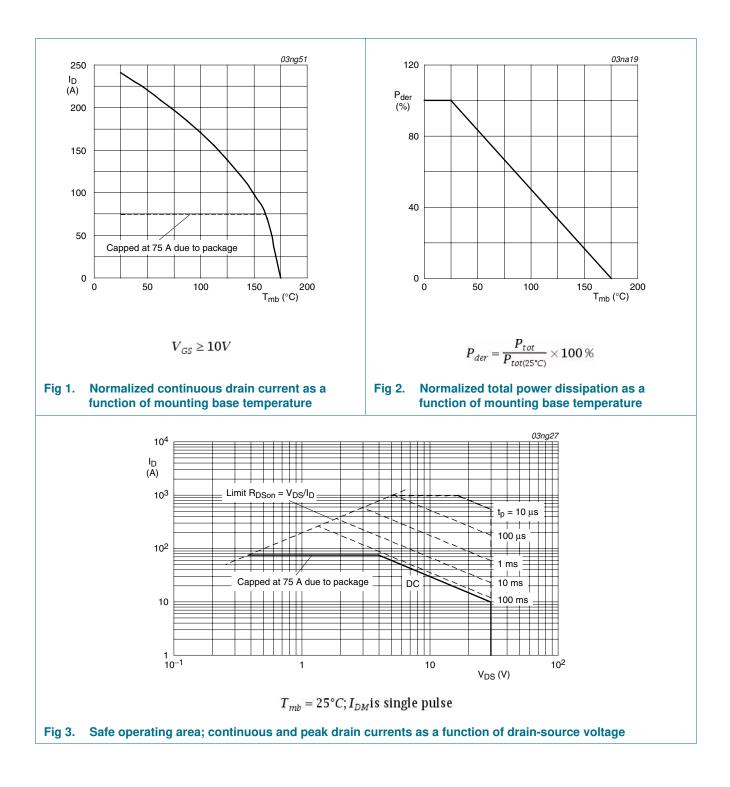
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mi	n <sup>.</sup>	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>i</sub> ≥ 25 °C; T <sub>i</sub> ≤ 175 °C	-			30	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-		_	30	V
V <sub>GS</sub>	gate-source voltage		-2(	).	-	20	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	<u>[1]</u> -		-	241	Α
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see Figure 1	[2] _		-	75	А
		$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{see } \frac{\text{Figure 1}}{\text{Figure 3}};$	[2] -		-	75	A
I <sub>DM</sub>	peak drain current	$T_{mb} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed};$ see <u>Figure 3</u>	-		-	967	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-		-	300	W
T <sub>stg</sub>	storage temperature		-55	5.	-	175	°C
Tj	junction temperature		-55	5.	-	175	°C
Source-drai	n diode						
ls	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u> _		-	241	А
			[2] _		-	75	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-		-	967	А
Avalanche r	uggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_{D} = 75 \; A; \; V_{sup} \leq 30 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; \text{unclamped} \end{array}$	-	•	-	2.3	J
		••• •					

[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

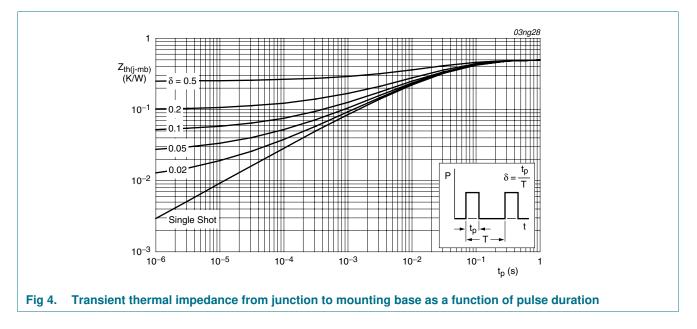
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### 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W



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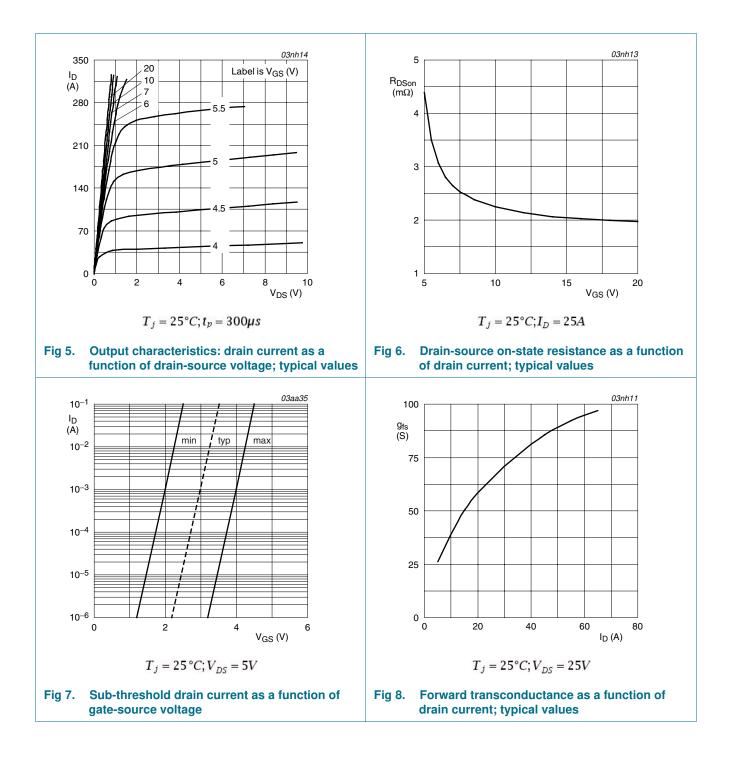
### 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub> drain-source brevoltage	drain-source breakdown	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	30	-	-	V
	voltage	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	2	3	4	V
		$\label{eq:ID} \begin{split} I_D &= 1 \text{ mA; } V_{DS} = V_{GS} \text{; } T_j = 175 \ ^\circ\text{C} \text{;} \\ \text{see } \frac{\text{Figure 10}}{10} \end{split}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	5.1	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	2.3	2.7	mΩ
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$	-	91	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	19	-	nC
Q <sub>GD</sub>	gate-drain charge		-	29	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	4659	6212	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	1691	2029	pF
C <sub>rss</sub>	reverse transfer capacitance		-	622	852	рF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_L$ = 1.2 Ω; $V_{GS}$ = 10 V;	-	31	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	107	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	113	-	ns
t <sub>f</sub>	fall time		-	118	-	ns
L <sub>D</sub>	internal drain inductance	from drain lead 6 mm from package to center of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; $T_{j}$ = 25 $^{\circ}\text{C}$	-	7.5	-	nH
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 40 \text{ A};  V_{GS} = 0  \text{V};  T_j = 25 ^\circ\text{C};$ see Figure 15	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s};$	-	88	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	132	-	nC

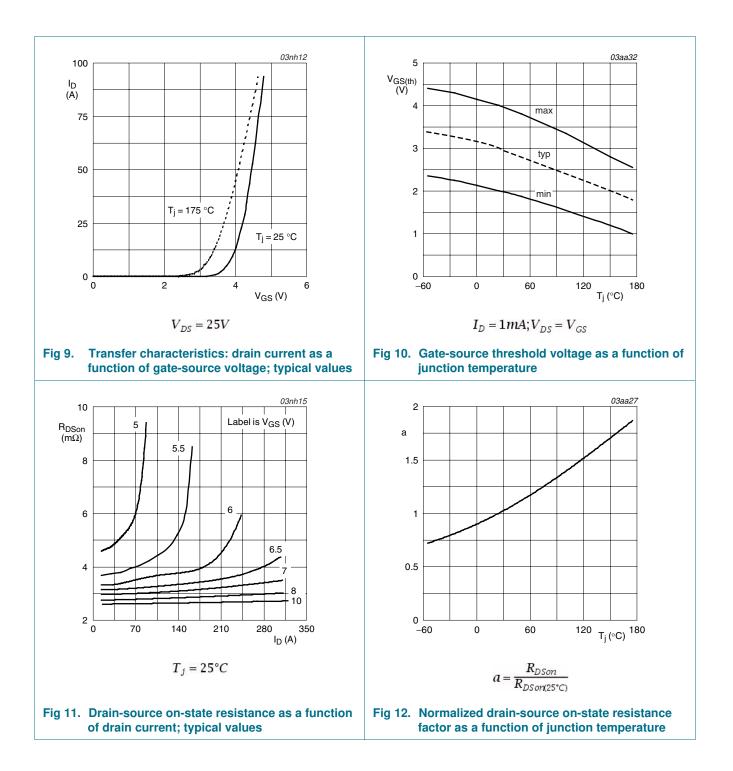
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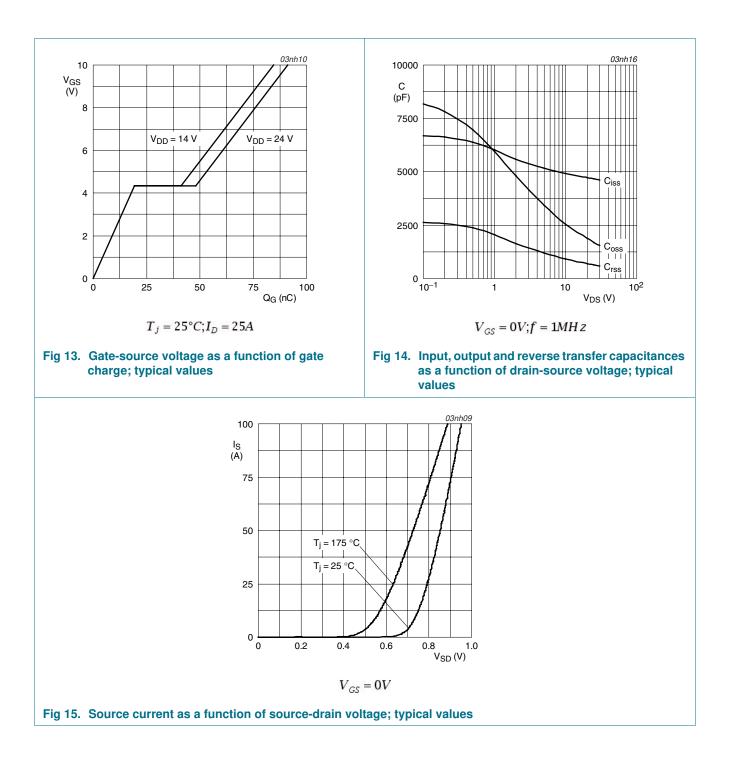
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### 7. Package outline

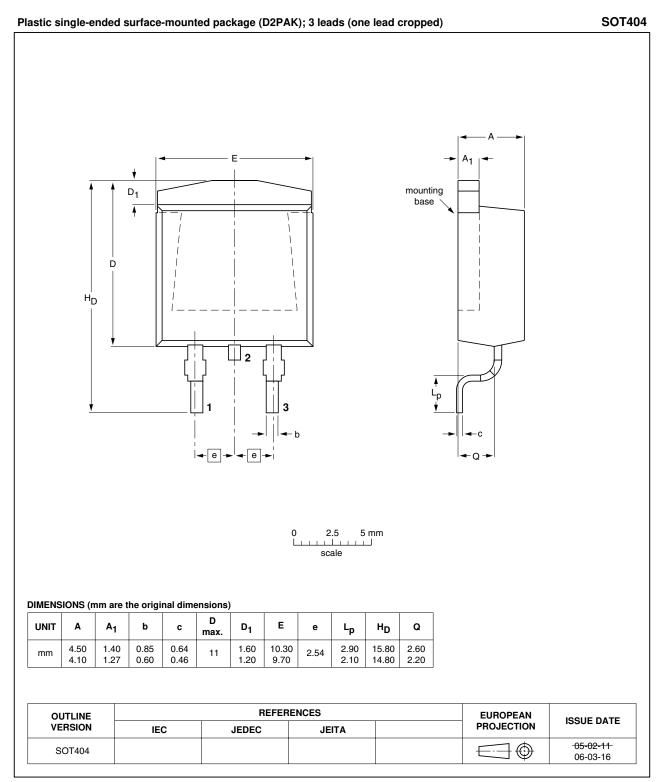


Fig 16. Package outline SOT404 (D2PAK)

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### 8. Revision history

Table 7. Revision history	1			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK762R7-30B v.4	20100608	Product data sheet	-	BUK75_76_7E2R7_30B v.3
Modifications:	guidelines <ul> <li>Legal texts</li> </ul>	of NXP Semiconductors s have been adapted to t	he new company n	comply with the new identity ame where appropriate. eet BUK75_76_7E2R7_30B v.3.
BUK75_76_7E2R7_30B v.3 (9397 750 12048)	20031013	Product data	-	-

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### 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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